M1MA141WKT1G, M1MA142WKT1G, SM1MA142WKT1G,

Common Cathode Silicon Dual Switching Diode

This Common Cathode Silicon Epitaxial Planar Dual Diode is designed for use in ultra high speed switching applications. This device is housed in the SC-70 package which is designed for low power surface mount applications.

Features

- Fast t_{rr} , < 3.0 ns
- Low C_D , < 2.0 pF
- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Reverse Voltage M1MA141WKT1G M1MA142WKT1G, SM1MA142WKT1G	V _R	40 80	Vdc
Peak Reverse Voltage M1MA141WKT1G M1MA142WKT1G, SM1MA142WKT1G	V _{RM}	40 80	Vdc
Forward Current Single Dual	I _F	100 150	mAdc
Peak Forward Current Single Dual	I _{FM}	225 340	mAdc
Peak Forward Surge Current M1MA141WKT1G M1MA142WKT1G, SM1MA142WKT1G	I _{FSM} (Note 1)	500 750	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	P_{D}	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	–55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. t = 1 SEC

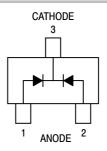


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SC-70 (SOT-323) CASE 419 STYLE 5



MARKING DIAGRAM



Mx = Device Code x = T for 141

U for 141

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]			
M1MA141WKT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel			
M1MA142WKT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel			
SM1MA142WKT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

^{*}Date Code orientation may vary depending upon manufacturing location.

${\tt M1MA141WKT1G,\,M1MA142WKT1G,\,SM1MA142WKT1G,}$

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Condition	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current M1MA141WKT1G M1MA142WKT1G, SM1MA142WKT1G	V _R = 35 V V _R = 75 V	I _R	- -	0.1 0.1	μAdc
Forward Voltage	I _F = 100 mA	V _F	=	1.2	Vdc
Reverse Breakdown Voltage M1MA141WKT1G M1MA142WKT1G, SM1MA142WKT1G	I _R = 100 μA	V _R	40 80	-	Vdc
Diode Capacitance	V _R = 0, f = 1.0 MHz	C _D	-	2.0	pF
Reverse Recovery Time (Figure 1)	I_F = 10 mA, V_R = 6.0 V, R_L = 100 Ω , I_{rr} = 0.1 I_R	t _{rr} (Note 2)	-	3.0	ns

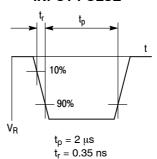
^{2.} t_{rr} Test Circuit

M1MA141WKT1G, M1MA142WKT1G, SM1MA142WKT1G,

RECOVERY TIME EQUIVALENT TEST CIRCUIT

A RL

INPUT PULSE



OUTPUT PULSE

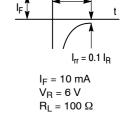
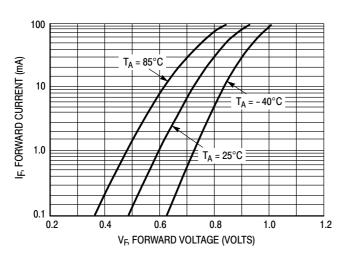


Figure 1. Recovery Time Equivalent Test Circuit



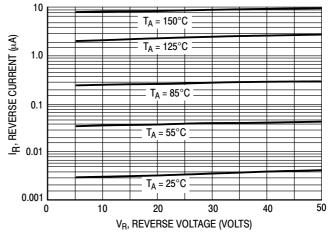


Figure 2. Forward Voltage

Figure 3. Reverse Current

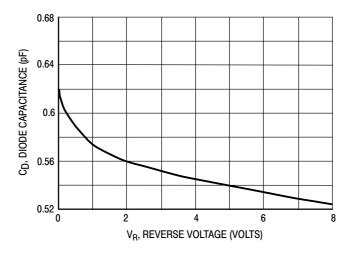


Figure 4. Diode Capacitance





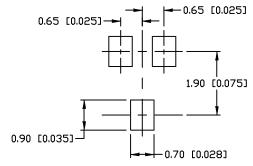
SC-70 (SOT-323) CASE 419 ISSUE P

DATE 07 OCT 2021

NOTES:

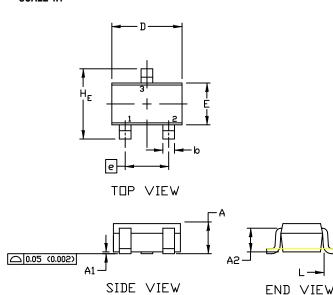
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF		0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Ε	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095
				`		



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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